DATARAM
Accelerating Innovation

DVM16S2L8/4G
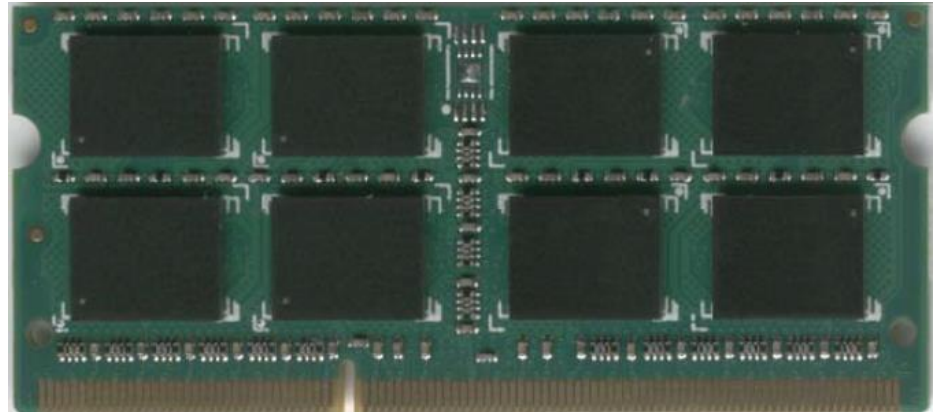**4GB - 204-Pin 2Rx8 Unbuffered Non-ECC LV DDR3 SODIMM**

Identification
DVM16S2L8/4G 512Mx64
4GB 2Rx8 PC3L-12800S-11

Performance Range
Clock / Module Speed / CL-t$_{RCD}$ –t$_{RP}$
800 MHz / DDR3L-1600 / 11-11-11
667 MHz / DDR3L-1333 / 10-10-10
667 MHz / DDR3L-1333 / 9-9-9
533 MHz / DDR3L-1066 / 8-8-8
533 MHz / DDR3L-1066 / 7-7-7
400 MHz / DDR3L-800 / 6-6-6
333 MHz / DDR3L-667 / 5-5-5

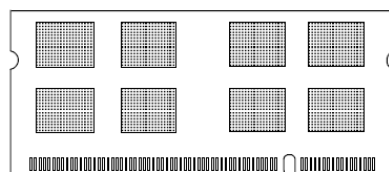| Features	Description
204-pin JEDEC-compliant SO-DIMM, 67.60 mm wide by 30.00 mm high Operating Voltage: VDD = VDDQ = +1.35V (1.283V to 1.45V) Backward-compatible to VDD = VDDQ = +1.5V ±0.075V I/O Type: SSTL_15 Data Transfer Rate: 12.8 Gigabytes/sec Data Bursts: 8 and burst chop 4 mode ZQ Calibration for Output Driver and On-Die Termination (ODT) Programmable ODT / Dynamic ODT during Writes Programmable CAS Latency: 5, 6, 7, 8, 9, 10 and 11 Differential Data Strobe signals SDRAM Addressing (Row/Col/Bank): 15/10/3 Fully RoHS Compliant	**DVM16S2L8/4G** is a non-ECC Unbuffered 512Mx64 small –outline memory module, which conforms to JEDEC's DDR3L-12800, PC3-1600 standard. The assembly is Dual-Rank. Each rank is comprised eight 256Mbx8 DDR3-1600 SDRAMs. One EEPROM is used for Serial Presence Detect. Both output driver strength and input termination impedance are programmable to maintain signal integrity on the I/O signals in a Fly-by topology.

Front view
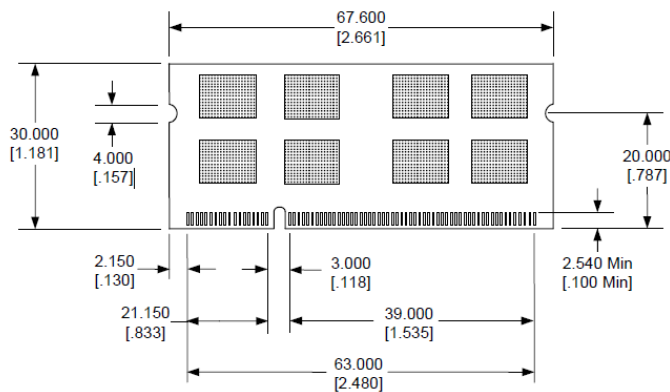
Notes

Tolerances on all dimensions except where otherwise indicated are ±.13 (.005).

All dimensions are expressed in millimeters [inches]

Back view

Side view